TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16652FT

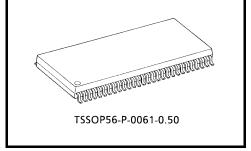
Low-Voltage 16-Bit Bus Transceiver/Register with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16652FT is a high-performance CMOS 16-bit bus transceiver/register. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V.$

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

All inputs are equipped with protection circuits against static discharge.



Weight: 0.25 g (typ.)

Features (Note)

- Low-voltage operation: $V_{CC} = 1.8 \text{ to } 3.6 \text{ V}$
- High-speed operation: $t_{pd} = 2.9 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V)}$

 $t_{pd} = 3.5 \text{ ns (max) (V}_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

 $: t_{pd} = 7.0 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

Output current: I_{OH}/I_{OL} = ±24 mA (min) (V_{CC} = 3.0 V)

 $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

: Human body model $> \pm 2000 \text{ V}$

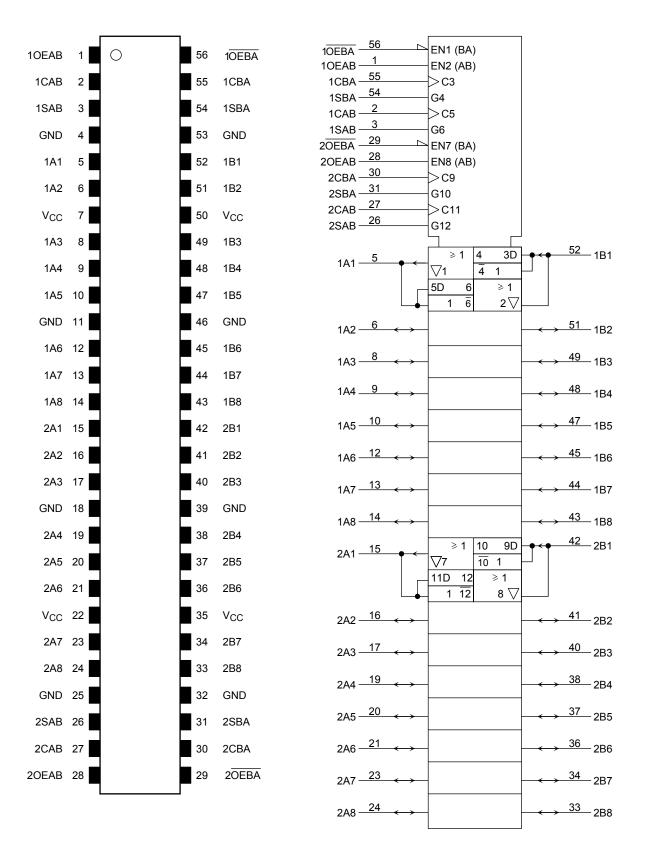
- Package: TSSOP (thin shrink small outline package)
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection is provided on all inputs and outputs

Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)

IEC Logic Symbol



Truth Table

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		Contro	I Inputs			Ві	JS	Function
OEAB	OEBA	CAB	CBA	SAB	SBA	Α	В	- Function
		X*	X*	Х	Х	Input	Input	The output functions of A and B Busses are
L	Н	^*	^*	^	^	Z	Z	disabled.
	П	4		X	X	X	X	Both A and B Busses are used as inputs to the internal flip-flops. Data on the Bus will be stored on the rising edge of the Clock.
						Input	Output	
		X*	X*	L	X	L	L	The data on the A bus are displayed on the B bus.
						Н	Н	
		$ \uparrow $	X*	L	X	L	L	The data on the A bus are displayed on the B Bus, and are stored into the A storage
Н	Н		^.	L	^	Н	Н	flip-flops on the rising edge of CAB.
		X*	X*	Н	х	х	Qn	The data in the A storage flop-flops are displayed on the B Bus.
		•				L	L	The data on the A Bus are stored into the A
			X*	Н	X	Н	Н	storage flip-flops on the rising edge of CAB, and the stored data propagate directly onto the B Bus.
						Output	Input	
		X*	X*	X	L		The data on the B Bus are displayed on the A bus.	
						н н		
		X*		Х	L	L	L	The data on the B Bus are displayed on the A Bus, and are stored into the B storage
L	L	Λ.		^	L	Н	Н	flip-flops on the rising edge of CBA.
		X*	X*	X	Н	Qn	X	The data in the B storage flip-flops are displayed on the A Bus.
			★			L	L	The data on the B Bus are stored into the B
		X*		X	Н	Н	Н	storage flip-flops on the rising edge of CBA, and the stored data propagate directly onto the A Bus.
						Output	Output	
Н	L	X*	X*	Н	Н	Qn	Qn	The data in the A storage flop-flops are displayed on the B Bus, and the data in the B storage flop-flops are displayed on the A.

X: Don't care

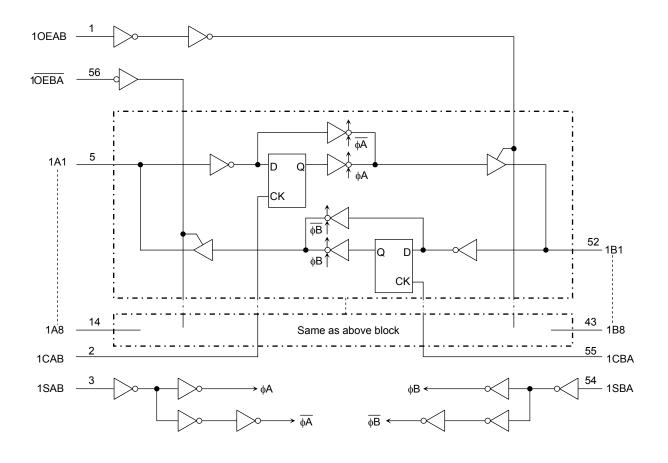
Z: High impedance

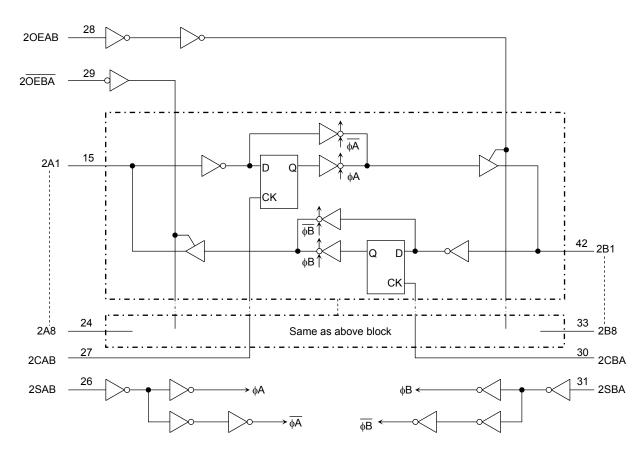
Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

*: The clocks are not internally gated with either OEAB or OEBA.

Therfore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

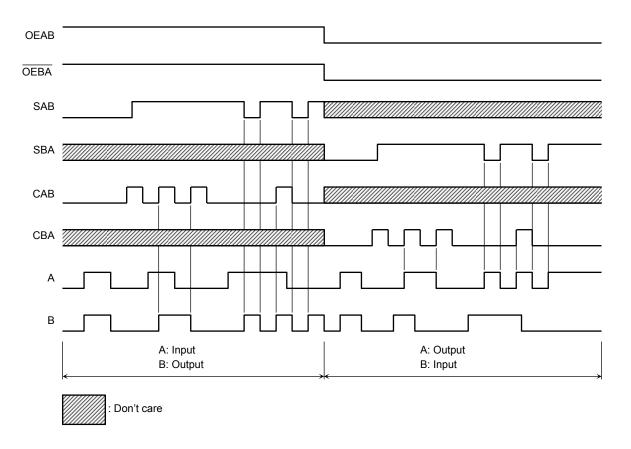
System Diagram





Timing Chart

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Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage (CAB, CBA, SAB, SBA, OEAB, OEBA)	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC bus I/O voltage	V _{I/O}	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	Vcc	1.8 to 3.6	V	
Tower supply voltage	VCC	1.2 to 3.6 (Note 2)	V	
Input voltage (CAB, CBA, SAB, SBA, OEAB, OEBA)	V_{IN}	-0.3 to 3.6	V	
Bus I/O voltage	Viva	0 to 3.6 (Note 3)	V	
Bus I/O voltage	V _{I/O}	0 to V _{CC} (Note 4)	V	
		±24 (Note 5)		
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA	
		±6 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{\text{CC}} \leq 3.6 \text{ V})$

Characteris	stics	Symbol	Test Co	ondition	V _{CC} (V)	Min	Max	Unit
Innut voltage	H-level	V _{IH}	-			2.0	_	V
Input voltage	L-level	V _{IL}	-	_	2.7 to 3.6	_	0.8	V
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2		
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -12 mA	2.7	2.2		
				$I_{OH} = -18 \text{ mA}$	3.0	2.4		
Output voltage				I _{OH} = -24 mA	3.0	2.2		V
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 100 \ \mu A$	2.7 to 3.6	_	0.2	
				I _{OL} = 12 mA	2.7	_	0.4	
				I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μΑ
2 state output OFF	otata aurrant	la-	$V_{IN} = V_{IH}$ or V_{IL}		0.71.00		±10.0	μА
3-state output OFF state current		loz	V _{OUT} = 0 to 3.6 V		2.7 to 3.6		±10.0	μΑ
Power-off leakage current		I _{OFF}	V_{IN} , $V_{OUT} = 0$ to 3.6 V		0	_	10.0	μΑ
Quiocoont cumply current		Icc	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0	
Quiescent supply ct	Quiescent supply current		$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7 to 3.6	_	±20.0	μΑ
Increase in I _{CC} per	input	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	istics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}		_		1.6	_	V
Input voltage	L-level	V _{IL}		_	2.3 to 2.7	_	0.7	V
Output voltage				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_	
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.3	2.0	_	
				I _{OH} = -12 mA	2.3	1.8	_	V
				I _{OH} = -18 mA	2.3	1.7	_	
	L-level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \ \mu A$	2.3 to 2.7	_	0.2	
				I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μА
3-state output OFF state current		1	V _{IN} = V _{IH} or V _{IL}		0.2 to 0.7		±10.0	
		loz	V _{OUT} = 0 to 3.6 V		2.3 to 2.7		±10.0	μΑ
Power-off leakage current		loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Outros and a second			V _{IN} = V _{CC} or GND		2.3 to 2.7	_	20.0	
Quiescent supply c	uneni	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3 to 2.7	_	±20.0	μА



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Co	ondition		Min	Max	Unit
		Cymbol	rest defidition		V _{CC} (V)	IVIIII	IVIAX	Onit
Input voltage H-level L-level		V _{IH}	_		1.8 to 2.3	0.7 × V _{CC}	_	V
		V _{IL}	_		1.8 to 2.3	_	0.2 × V _{CC}	V
H-level		Voh	V _{IN} = V _{IH} or V _{II}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				I _{OH} = -6 mA	1.8	1.4	_	V
	L-level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	1.8		0.2	
				I _{OL} = 6 mA	1.8		0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0 to 3.6 V		1.8		±5.0	μΑ
3-state output OFF state current		l _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		1.8	_	±10.0	μА
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ
Ouis seemt suggest suggest		Icc	V _{IN} = V _{CC} or GND		1.8		20.0	μА
Quiescent supply co	Quiescent supply current		$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8		±20.0	μΑ

AC Characteristics (Ta = -40 to 85°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$) (Note 1)

Characteristics	Symbol	Test Condition	Min		Max	Unit
	ĺ		V _{CC} (V)			
			1.8	100	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 3	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
Propagation delay time	.		1.8	1.5	7.0	
(An, Bn-Bn, An)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	8.0	3.5	ns
(אוז, טוויטוז, אוז)	t _{pHL}		3.3 ± 0.3	0.6	2.9	
Drangation delay time	4		1.8	1.5	8.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 3	2.5 ± 0.2	0.8	4.4	ns
(CAB, CBA-Bn, An)	t _{pHL}		3.3 ± 0.3	0.6	3.2	
Decree and in the delegation			1.8	1.5	8.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.4	ns
(SAB, SBA-Bn, An)	t _{pHL}		3.3 ± 0.3	0.6	3.5	
0.1.1.1.11	t _{pZL}	Figure 1, Figure 4, Figure 5	1.8	1.5	9.8	
Output enable time			2.5 ± 0.2	0.8	4.9	ns
(OEAB, OEBA -An, Bn)			3.3 ± 0.3	0.6	3.8	
Outsid disable time	1		1.8	1.5	8.1	ns
Output disable time	t _{pLZ}	Figure 1, Figure 4, Figure 5	2.5 ± 0.2	0.8	4.5	
(OEAB, OEBA -An, Bn)	t _{pHZ}		3.3 ± 0.3	0.6	3.9	
			1.8	4.0	_	
Minimum pulse width	t _{w (H)}	Figure 1, Figure 3	2.5 ± 0.2	1.5	_	ns
	t _{w (L)}		3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum setup time	ts	Figure 1, Figure 3	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	th	Figure 1, Figure 3	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
	1.		1.8	_	0.5	
Output to output skew	tosLH	(Note 2)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

9

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design. $(t_{OSLH} = |t_{DLHm} - t_{DLHn}|, \, t_{OSHL} = |t_{DHLm} - t_{DHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}, C_L = 30 \text{ pF}, R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition		T	Тур.	Unit
	Í			V _{CC} (V)	,,	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	0.6	V
, 52		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	8.0	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	-0.25	٧
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	-0.8	
	V _{OHV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	1.8	1.5	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	2.5	1.9	V
, on		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	ote)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

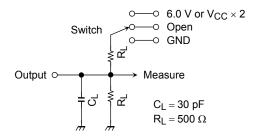
Characteristics Symb		Test Condition	V _{CC} (V)	Тур.	Unit
Input capacitance	C _{IN}	(OEAB, OEBA, CAB, CBA, SAB, SBA)	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	An, Bn	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch			
t _{pLH} , t _{pHL}	Open			
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$			
t _{pHZ} , t _{pZH}	GND			

Figure 1

AC Waveform

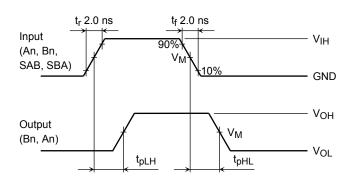


Figure 2 t_{pLH} , t_{pHL}

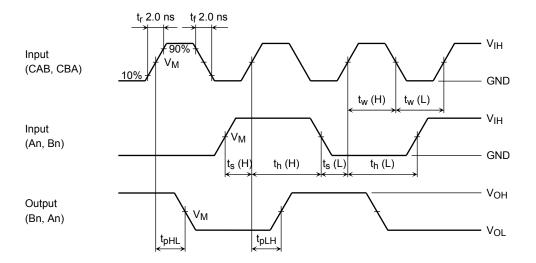


Figure 3 tpLH, tpHL, tw, ts, th

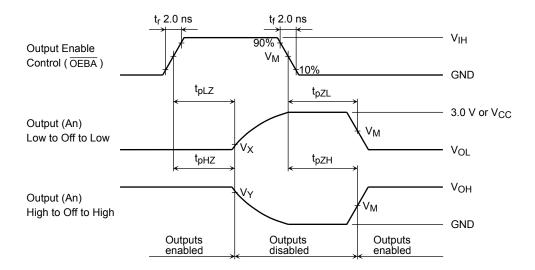


Figure 4 $t_{\text{pLZ}},\,t_{\text{pHZ}},\,t_{\text{pZL}},\,t_{\text{pZH}}$

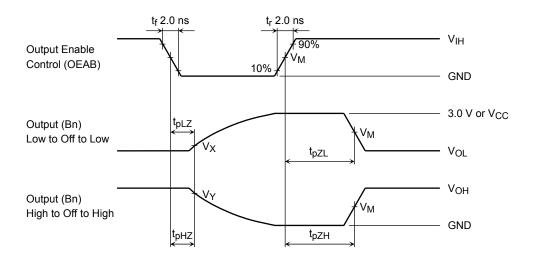
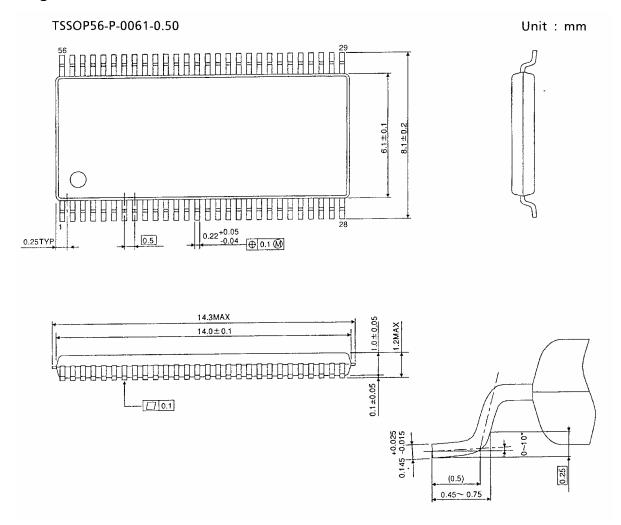


Figure 5 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V_{IH}	2.7 V	V _{CC}	V _{CC}
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
V_{Y}	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

12 2006-02-01

Package Dimensions



Weight: 0.25 g (typ.)

Note: Lead (Pb)-Free Packages

TSSOP56-P-0061-0.50

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20070701-EN

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